# 20V N-Channel Enhancement Mode MOSFET

The JXP3416EVRG uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and high density cell Design for ultra low on-resistance. This device is suitable for use as a load switch or in PWM applications.

$V_{DS}$ =20V $I_D$ =6.5A
$R_{DS(ON)}$(Typ.)=18 @$V_{GS}$=2.5V
$R_{DS(ON)}$(Typ.)=15 @$V_{GS}$=4.5V
High power and current handing capability
Lead free product is acquired
Surface mount package
ESD Rating: 3500V HBM

PWM applications
Load switch

SOT-23

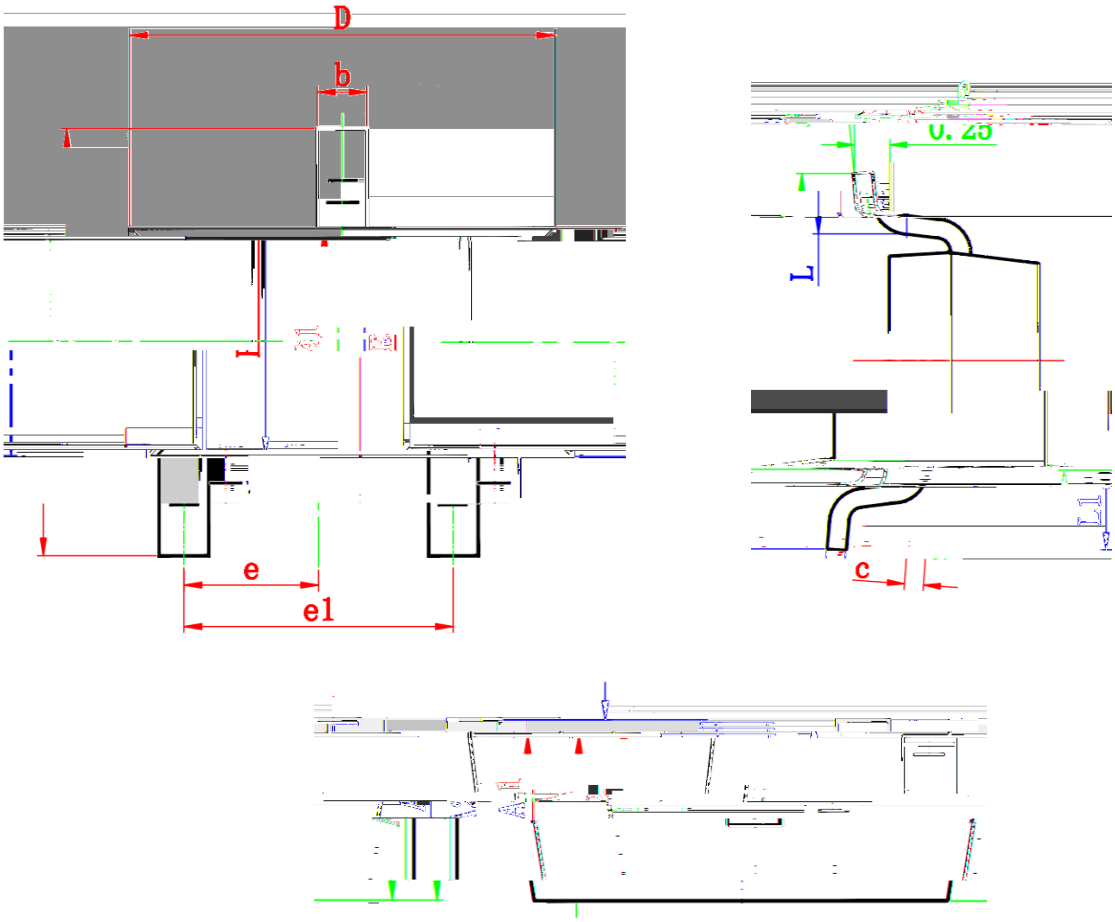
| Part Number | Storage Temperature | Package | Marking | Devices Per Reel |
|---|---|---|---|---|
| JXP3416ERG | -55°C to +150°C | SOT-23 | 3416E | 3000 |

**(TA=25 unless otherwise noted)**

| parameter | symbol | limit | unit |
|---|---|---|---|

| Parameter | Symbol | |
|---|---|---|

**SOT-23**




| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|---|---|---|---|---|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | | |